# 20 V, 1 A PNP medium power transistor Rev. 06 — 2 December 2008

**Product data sheet** 

# 1. Product profile

## 1.1 General description

PNP medium power transistor in a Surface-Mounted Device (SMD) plastic package.

Table 1. **Product overview** 

Type number[1]	Package		Package
	NXP	JEITA	configuration
BCP69	SOT223	SC-73	medium power
BCP69-16			
BCP69-16/DG			
BCP69-16/IN			
BCP69-25			

<sup>[1] /</sup>DG: halogen-free

#### 1.2 Features

- High current
- Three current gain selections
- 1.4 W total power dissipation
- Medium power SMD plastic package

# 1.3 Applications

- Linear voltage regulators
- High-side switches
- Supply line switches
- MOSFET drivers
- Audio preamplifier

# 1.4 Quick reference data

Table 2. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{CEO}$	collector-emitter voltage	open base	-	-	-20	V
I <sub>C</sub>	collector current		-	-	<b>–1</b>	Α
$I_{CM}$	peak collector current	single pulse; $t_n \le 1 \text{ ms}$	-	-	-2	Α



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Table 2. Quick reference data ... continued

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
h <sub>FE</sub>	DC current gain	$V_{CE} = -1 \text{ V};$ $I_{C} = -500 \text{ mA}$				
	BCP69		85	-	375	
	BCP69-16 BCP69-16/DG		100	-	250	
	BCP69-16/IN		140	-	230	
	BCP69-25		160	-	375	

# 2. Pinning information

Table 3. Pinning

Tubic o.	· ····································		
Pin	Description	Simplified outline	Graphic symbol
1	base		
2	collector	4	2, 4
3	emitter		1 —
4	collector		3
			sym028

# 3. Ordering information

Table 4. Ordering information

Type number[1]	Package					
	Name	Description	Version			
BCP69	SC-73	plastic surface-mounted package with increased	SOT223			
BCP69-16		heatsink; 4 leads				
BCP69-16/DG						
BCP69-16/IN						
BCP69-25						

<sup>[1] /</sup>DG: halogen-free

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# 4. Marking

Table 5. Marking codes

Type number[1]	Marking code
BCP69	BCP69
BCP69-16	BCP69/16
BCP69-16/DG	BCP69-16D
BCP69-16/IN	69-16N
BCP69-25	BCP69/25

<sup>[1] /</sup>DG: halogen-free

# 5. Limiting values

Table 6. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

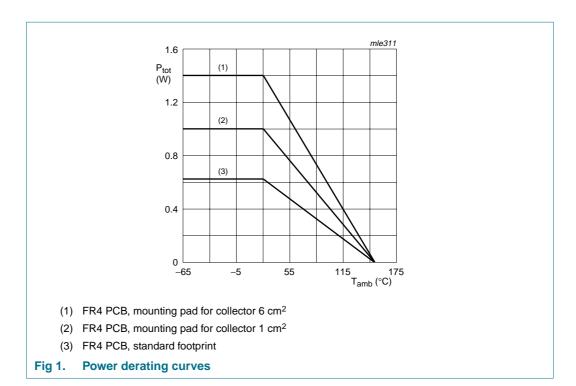
Symbol	Parameter	Conditions	Min	Max	Unit
$V_{CBO}$	collector-base voltage	open emitter	-	-32	V
$V_{CEO}$	collector-emitter voltage	open base	-	-20	V
$V_{EBO}$	emitter-base voltage	open collector	-	-5	V
I <sub>C</sub>	collector current		-	-1	Α
I <sub>CM</sub>	peak collector current	single pulse; $t_p \le 1 \text{ ms}$	-	-2	Α
I <sub>BM</sub>	peak base current	single pulse; $t_p \le 1 \text{ ms}$	-	-200	mA
P <sub>tot</sub>	total power dissipation	$T_{amb} \le 25  ^{\circ}C$	<u>[1]</u> _	0.625	W
			[2] _	1	W
			[3] _	1.4	W
Tj	junction temperature		-	150	°C
T <sub>amb</sub>	ambient temperature		-65	+150	°C
T <sub>stg</sub>	storage temperature		-65	+150	°C

<sup>[1]</sup> Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

<sup>[2]</sup> Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm<sup>2</sup>.

<sup>[3]</sup> Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm<sup>2</sup>.

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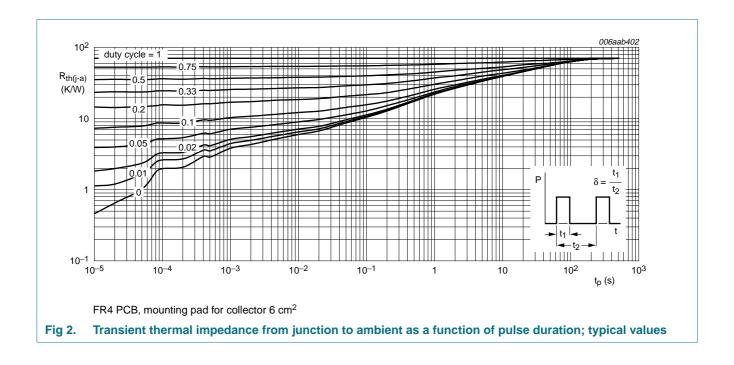
# 6. Thermal characteristics

Table 7. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>th(j-a)</sub>	thermal resistance from junction	-	<u>[1]</u> _	-	200	K/W
	to ambient		[2] _	-	125	K/W
			[3] _	-	89	K/W
$R_{th(j-sp)}$	thermal resistance from junction to solder point		-	-	15	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm<sup>2</sup>.
- [3] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm<sup>2</sup>.

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# 7. Characteristics

Table 8. Characteristics

 $T_{amb} = 25 \,^{\circ}C$  unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I <sub>CBO</sub>	collector-base cut-off	$V_{CB} = -25 \text{ V}; I_E = 0 \text{ A}$	-	-	-100	nA
	current	$V_{CB} = -25 \text{ V}; I_E = 0 \text{ A};$ $T_j = 150 ^{\circ}\text{C}$	-	-	-10	μΑ
I <sub>EBO</sub>	emitter-base cut-off current	$V_{EB} = -5 \text{ V}; I_C = 0 \text{ A}$	-	-	-100	nA
h <sub>FE</sub>	DC current gain					
	BCP69	$V_{CE} = -10 \text{ V};$ $I_{C} = -5 \text{ mA}$	50	-	-	
		$V_{CE} = -1 \text{ V};$ $I_{C} = -500 \text{ mA}$	85	-	375	
		$V_{CE} = -1 \ V; \ I_{C} = -1 \ A$	60	-	-	
	BCP69-16 BCP69-16/DG	$V_{CE} = -1 \text{ V};$ $I_{C} = -500 \text{ mA}$	100	-	250	
	BCP69-16/IN	$V_{CE} = -1 \text{ V};$ $I_{C} = -500 \text{ mA}$	140	-	230	
	BCP69-25	$V_{CE} = -1 \text{ V};$ $I_{C} = -500 \text{ mA}$	160	-	375	
$V_{CEsat}$	collector-emitter saturation voltage	$I_{C} = -1 A;$ $I_{B} = -100 \text{ mA}$	-	-	-500	mV
$V_{BE}$	base-emitter voltage	$V_{CE} = -10 \text{ V};$ $I_{C} = -5 \text{ mA}$	-	-	-700	mV
		$V_{CE} = -1 \text{ V}; I_{C} = -1 \text{ A}$	-	-	-1	V
C <sub>c</sub>	collector capacitance	$V_{CB} = -10 \text{ V};$ $I_E = i_e = 0 \text{ A};$ $f = 1 \text{ MHz}$	-	28	-	pF
f <sub>T</sub>	transition frequency	$V_{CE} = -5 \text{ V};$ $I_{C} = -50 \text{ mA};$ $f = 100 \text{ MHz}$	40	140	-	MHz

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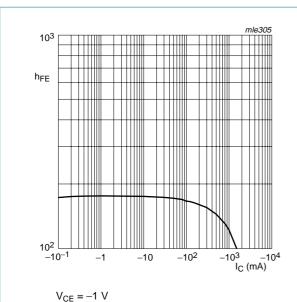
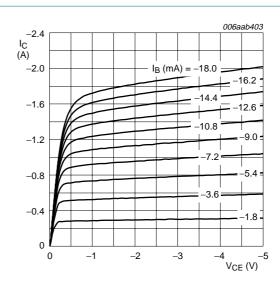
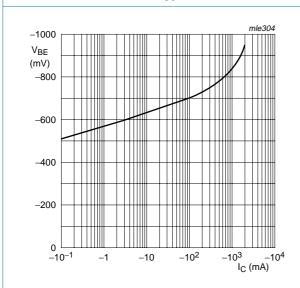


Fig 3. BCP69-16: DC current gain as a function of collector current; typical values



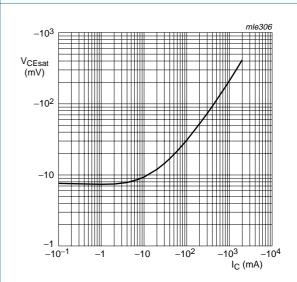
 $T_{amb} = 25 \, ^{\circ}C$ 

Fig 4. BCP69-16: Collector current as a function of collector-emitter voltage; typical values



 $V_{CE} = -1 \text{ V}$ Fig 5. BCP69-16: Base-emitter voltage as a function

of collector current; typical values



 $I_{\rm C}/I_{\rm B} = 10$ 

Fig 6. BCP69-16: Collector-emitter saturation voltage as a function of collector current; typical values

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#### 20 V, 1 A PNP medium power transistor

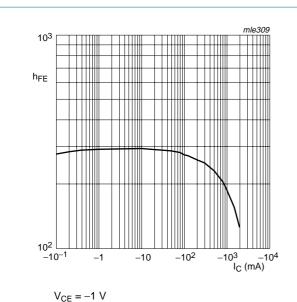
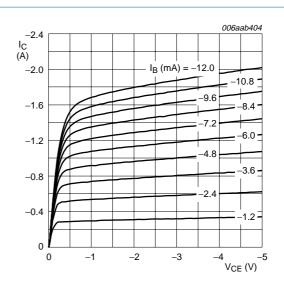


Fig 7. BCP69-25: DC current gain as a function of collector current; typical values



 $T_{amb} = 25 \, ^{\circ}C$ 

Fig 8. BCP69-25: Collector current as a function of collector-emitter voltage; typical values

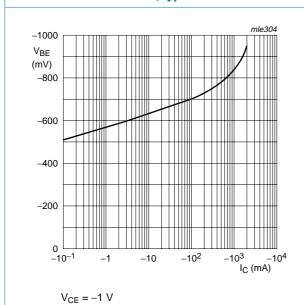
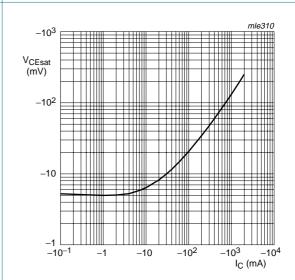


Fig 9. BCP69-25: Base-emitter voltage as a function of collector current; typical values



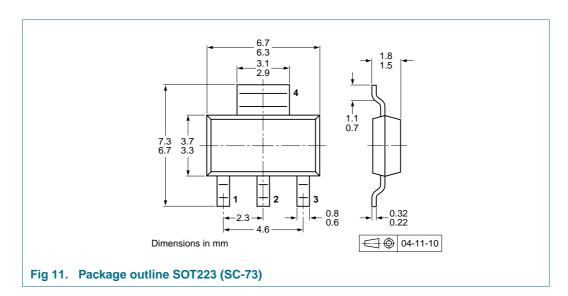
 $I_{\rm C}/I_{\rm B}=10$ 

Fig 10. BCP69-25: Collector-emitter saturation voltage as a function of collector current; typical values

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# 8. Package outline



# 9. Packing information

Table 9. Packing methods

The indicated -xxx are the last three digits of the 12NC ordering code.[1]

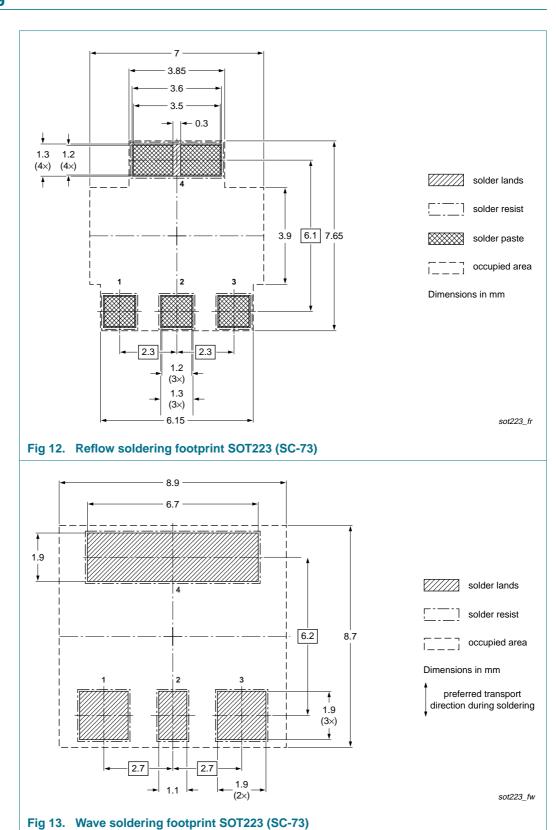
Type number[2]	Package	ge Description Packing		g quantity	
			1000	4000	
BCP69	SOT223	8 mm pitch, 12 mm tape and reel	-115	-135	
BCP69-16					
BCP69-16/DG					
BCP69-16/IN					
BCP69-25					

<sup>[1]</sup> For further information and the availability of packing methods, see  $\underline{\text{Section } 13}$ .

<sup>[2] /</sup>DG: halogen-free

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# 10. Soldering



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# 11. Revision history

## Table 10. Revision history

	- •					
Document ID	Release date	Data sheet status	Change notice	Supersedes		
BCP69_6	20081202	Product data sheet	-	BCP69_5		
Modifications:		f this data sheet has been red NXP Semiconductors.	designed to comply w	ith the new identity		
	<ul> <li>Legal texts h</li> </ul>	<ul> <li>Legal texts have been adapted to the new company name where appropriate.</li> </ul>				
	Table 1 "Product overview": enhanced					
	<ul> <li><u>Table 4 "Ordering information"</u>: enhanced</li> </ul>					
	• Figure 2, 4 and 8: updated					
	• <u>Figure 11</u> : su	perseded by minimized pack	age outline drawing			
	<ul> <li>Section 9 "Page 1</li> </ul>	acking information": added				
	<ul><li>Section 10 "S</li></ul>	Soldering": enhanced				
	<ul> <li>Section 12 "L</li> </ul>	<u>egal information"</u> : updated				
BCP69_5	20031125	Product specification	-	BCP69_4		
BCP69_4	20021115	Product specification	-	BCP69_3		
BCP69_3	19990408	Product specification	-	BCP69_CNV_2		

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# 12. Legal information

#### 12.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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